



BF 257 · BF 258 · BF 259

NPN HIGH VOLTAGE VIDEO AMPLIFIER

MICRO ELECTRONICS

THE BF257, BF258, BF259 ARE NPN SILICON PLANAR TRANSISTORS DESIGNED FOR HIGH VOLTAGE VIDEO OUTPUT STAGES IN BLACK-AND-WHITE AND COLOUR TV-RECEIVERS.

CASE TO-39

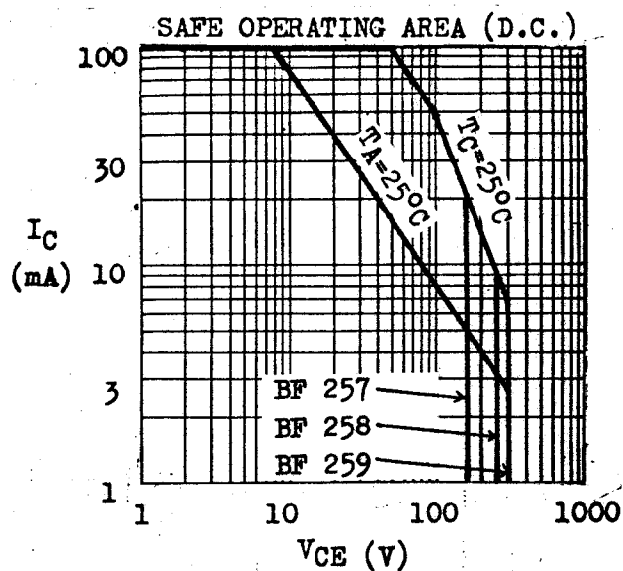
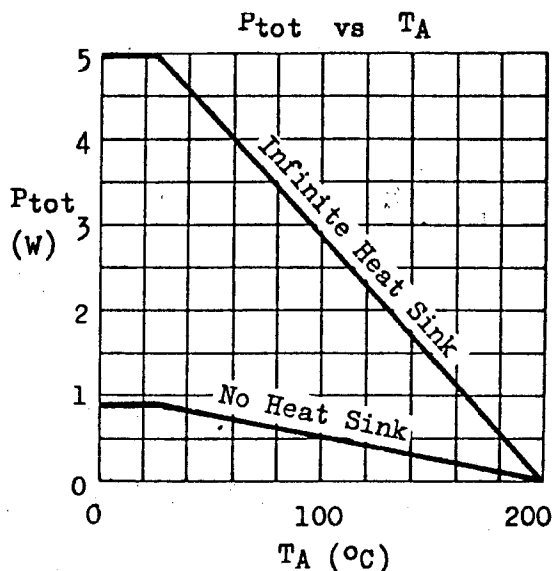


ABSOLUTE MAXIMUM RATINGS

		BF257	BF258	BF259
Collector-Base Voltage	V_{CBO}	160V	250V	300V
Collector-Emitter Voltage	V_{CEO}	160V	250V	300V
Emitter-Base Voltage	V_{EBO}		5V	
Collector Current	I_C		100mA	
Total Power Dissipation @ $T_C \leq 25^\circ C$ @ $T_A \leq 25^\circ C$	P_{tot}		5W	800mW
Operating Junction & Storage Temperature	T_j, T_{stg}		-65 to 200°C	

THERMAL RESISTANCE

Junction to Case	θ_{jc}	35°C/W	max.
Junction to Ambient	θ_{ja}	220°C/W	max.



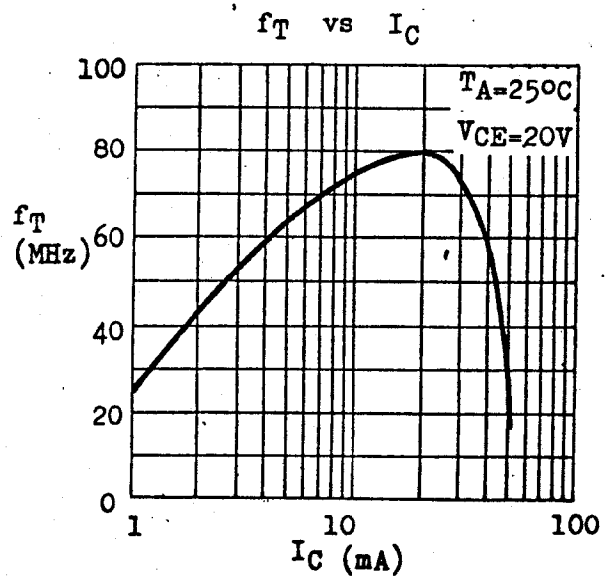
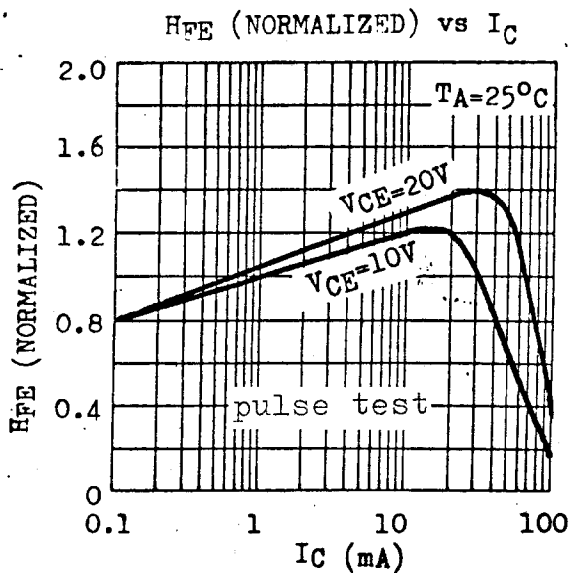
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PARAMETER	SYMBOL	BF257	BF258	BF259	UNIT	TEST CONDITIONS
		MIN MAX	MIN MAX	MIN MAX		
ollector-Base Breakdown Voltage	BV_{CBO}	160	250	300	V	$I_C=0.1mA$ $I_E=0$
ollector-Emitter Breakdown Voltage	LV_{CEO}^*	160	250	300	V	$I_C=10mA$ $I_B=0$
mitter-Base Breakdown Voltage	BV_{EBO}	5	5	5	V	$I_E=0.1mA$ $I_C=0$
ollector Cutoff Current	I_{CBO}	50	50	50	nA	$V_{CB}=100V$ $I_E=0$
					nA	$V_{CB}=200V$ $I_E=0$
					nA	$V_{CB}=250V$ $I_E=0$
mitter Cutoff Current	I_{EBO}	50	50	50	nA	$V_{EB}=3V$ $I_C=0$
.C. Current Gain	H_{FE}^*	25	25	25		$I_C=30mA$ $V_{CE}=10V$
ollector-Emitter Saturation Voltage	$V_{CE(sat)}^*$	1	1	1	V	$I_C=30mA$ $I_B=6mA$
urrent Gain-Bandwidth Product	f_T	50	50	50	MHz	$I_C=15mA$ $V_{CE}=20V$
ollector-Base Capacitance	C_{cb}	5	5	5	pF	$V_{CB}=30V$ $I_E=0$ $f=1MHz$

* Pulse Test : Pulse Width=0.3mS, Duty Cycle=1%



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